

EGP20A - EGP20K

2.0 Ampere Glass Passivated High Efficiency Rectifiers

Features

- Glass passivated cavity-free junction
- High surge current capability
- Low leakage current
- Superfast recovery time for high efficiency
- Low forward voltage, high current capability



DO-15 Glass case
COLOR BAND DENOTES CATHODE

Absolute Maximum Ratings* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
I_O	Average Rectified Current .375" lead length @ $T_L = 55^\circ\text{C}$	2.0	A
$I_{f(\text{surge})}$	Peak Forward Surge Current 8.3 ms single half-sine-wave Superimposed on rated load (JEDEC method)	75	A
P_D	Total Device Dissipation Derate above 25°C	3.13 25	W mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	15	°C/W
T_J, T_{STG}	Junction and Storage Temperature Range	-65 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

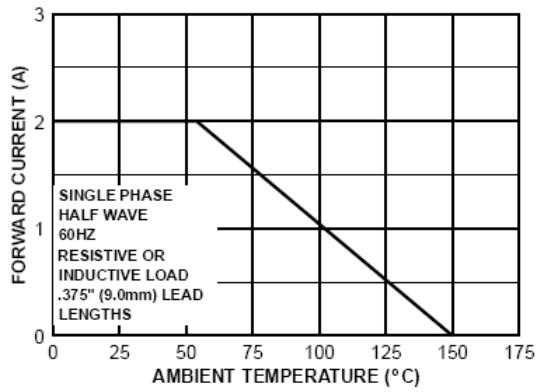
Electrical Characteristics* $T_a = 25^\circ\text{C}$ unless otherwise noted

Parameter	Device								Units
	20A	20B	20C	20D	20F	20G	20J	20K	
Peak Repetitive Reverse Voltage	50	100	150	200	300	400	600	800	V
Maximum RMS Voltage	35	70	105	140	210	280	420	560	V
DC Reverse Voltage (Rated V_R)	50	100	150	200	300	400	600	800	V
Maximum Reverse Current @ rated V_R $T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	5.0 100								μA μA
Maximum Reverse Recovery Time $I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{rr} = 0.25\text{ A}$	50						75		nS
Maximum Forward Voltage @ 2.0 A	0.95			1.25		1.7			V
Typical Junction Capacitance $V_R = 4.0\text{ V}$, $f = 1.0\text{ MHz}$	70			45					pF

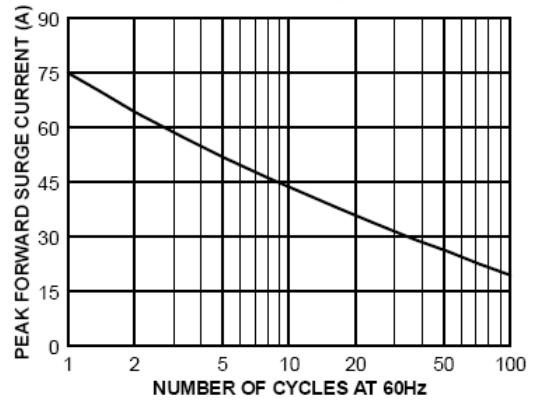
* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

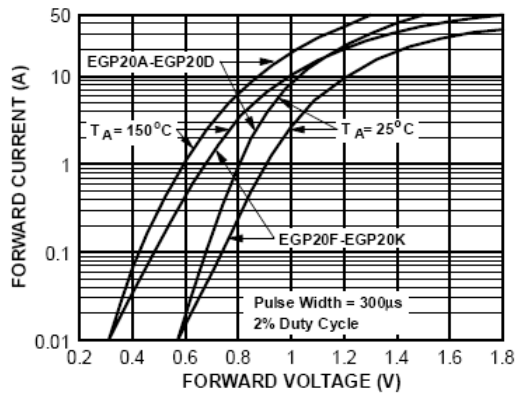
Forward Current Derating Curve



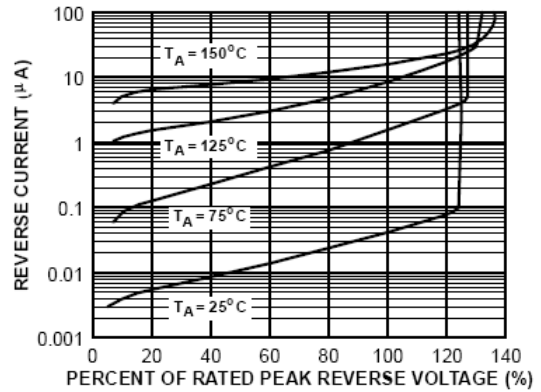
Non-Repetitive Surge Current



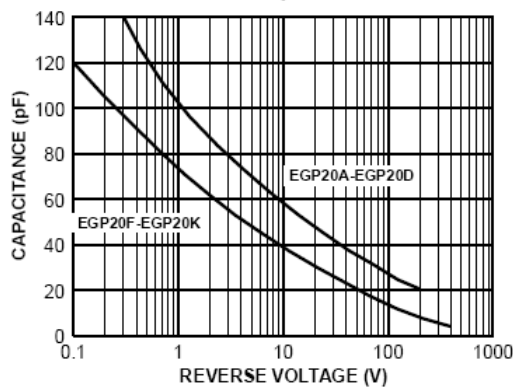
Forward Characteristics



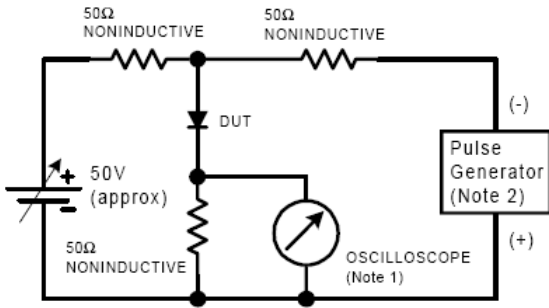
Reverse Characteristics



Junction Capacitance

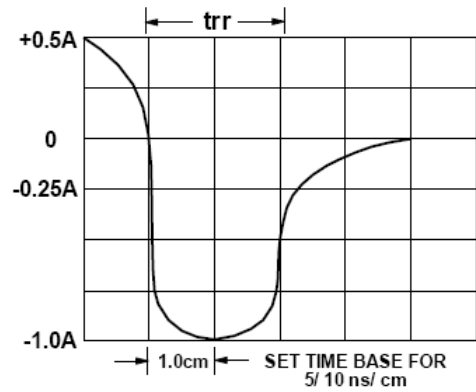


Reverse Recovery Time Characteristic and Test Circuit Diagram



NOTES:


1. Rise time = 7.0 ns max; Input impedance = 1.0 megaohm 22 pf.
2. Rise time = 10 ns max; Source impedance = 50 ohms.





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